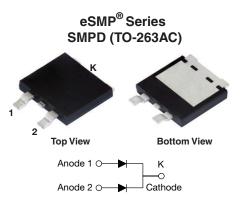
## Vishay Semiconductors

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### LINKS TO ADDITIONAL RESOURCES



| PRIMARY CHARACTERISTICS          |                 |  |  |  |  |
|----------------------------------|-----------------|--|--|--|--|
| I <sub>F(AV)</sub>               | 2 x 8 A         |  |  |  |  |
| V <sub>R</sub>                   | 200 V           |  |  |  |  |
| V <sub>F</sub> at I <sub>F</sub> | 0.77 V          |  |  |  |  |
| t <sub>rr</sub>                  | 27 ns           |  |  |  |  |
| T <sub>J</sub> max.              | 175 °C          |  |  |  |  |
| Package                          | SMPD (TO-263AC) |  |  |  |  |
| Circuit configuration            | Common cathode  |  |  |  |  |

#### FEATURES

• Hyperfast recovery time, reduced Q<sub>rr</sub>, and soft recovery



FREE

- 175 °C maximum operating junction temperature
- · Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, telecom, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

#### **MECHANICAL DATA**

Case: SMPD (TO-263AC)

Molding compound meets UL 94 V-0 flammability rating Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002

| ABSOLUTE MAXIMUM RATINGS          |            |                  |  |        |       |  |  |
|-----------------------------------|------------|------------------|--|--------|-------|--|--|
| PARAMETER                         |            | SYMBOL           | TEST CONDITIONS                            | VALUES | UNITS |  |  |
| Peak repetitive reverse voltage   |            | V <sub>RRM</sub> |  | 200    | V     |  |  |
| Average restified forward average | per device |                  | T <sub>solder pad</sub> = 155 °C           | 16     | ٨     |  |  |
| Average rectified forward current | per diode  | IF(AV)           |  | 8      |       |  |  |
| Non-repetitive peak surge current |            |                  | T 05 °C 6 mg aguara pulas 190              | А      |       |  |  |
| Non-repetitive peak surge current | per diode  | IFSM             | $T_J = 25 \ ^{\circ}C$ , 6 ms square pulse | 100    |       |  |  |

| <b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25 \ ^{\circ}C$ unless otherwise specified) |                 |   |      |      |      |       |  |
|---|-----------------|---|------|------|------|-------|--|
| PARAMETER   | SYMBOL          | TEST CONDITIONS                                 | MIN. | TYP. | MAX. | UNITS |  |
| Breakdown voltage, blocking voltage   | $V_{BR}, V_{R}$ | I <sub>R</sub> = 100 μA                         | 200  | -    | -    |       |  |
| Forward voltage, per diode  |                 | I <sub>F</sub> = 8 A                            | -    | 0.93 | 1.03 | V     |  |
|   |                 | I <sub>F</sub> = 8 A, T <sub>J</sub> = 150 °C   | -    | 0.77 | 0.87 |       |  |
| Devenue la classe commento a condicada  | I <sub>R</sub>  | $V_{R} = V_{R}$ rated                           | -    | -    | 2    |       |  |
| Reverse leakage current, per diode  |                 | $T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$ | -    | 6    | 100  | μΑ    |  |
| Junction capacitance, per diode   | CT              | V <sub>R</sub> = 200 V                          | -    | 23   | -    | pF    |  |

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| <b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified) |                  |  |   |      |      |       |    |
|---|------------------|--|---|------|------|-------|----|
| PARAMETER   | SYMBOL           | TEST CO  | MIN.  | TYP. | MAX. | UNITS |    |
|   |                  | $I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}$ | õs, V <sub>R</sub> = 30 V                                 | -    | 27   | -     |    |
| Bayaraa raaayary tima   | +                | $I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr}$           | -   | -    | 25   |       |    |
| Reverse recovery time   | t <sub>rr</sub>  | T <sub>J</sub> = 25 °C                                     |   | -    | 23   | -     | ns |
|   |                  | T <sub>J</sub> = 125 °C                                    | $I_F = 8 A,$  | -    | 35   | -     |    |
| Pools recovery ourrent  | I <sub>RRM</sub> | T <sub>J</sub> = 25 °C                                     |   | -    | 2.8  | -     | Α  |
| Peak recovery current   |                  | T <sub>J</sub> = 125 °C                                    | dl <sub>F</sub> /dt = 200 A/µs,<br>V <sub>B</sub> = 160 V | -    | 5    | -     | ~  |
| Deverse version shows   | 0                | T <sub>J</sub> = 25 °C                                     |   | -    | 30   | -     | nC |
| Reverse recovery charge   | Q <sub>rr</sub>  | T <sub>J</sub> = 125 °C                                    |   | -    | 90   | -     |    |

| THERMAL - MECHANICAL SPECIFICATIONS             |                                   |                            |      |      |      |       |  |
|---|-----------------------------------|----------------------------|------|------|------|-------|--|
| PARAMETER                                       | SYMBOL                            | TEST CONDITIONS            | MIN. | TYP. | MAX. | UNITS |  |
| Maximum junction and storage temperature range  | T <sub>J</sub> , T <sub>Stg</sub> |                            | -55  | -    | +175 | °C    |  |
| Thermal resistance, per diode junction to mount | R <sub>thJM</sub>                 |                            | -    | 1.8  | 2.5  | °C/W  |  |
| Approximate weight                              |                                   |                            |      | 0.55 |      | g     |  |
| Approximate weight                              |                                   |                            |      | 0.02 |      | oz.   |  |
| Marking device                                  |                                   | Case style SMPD (TO-263AC) |      | 16CI | DH02 |       |  |



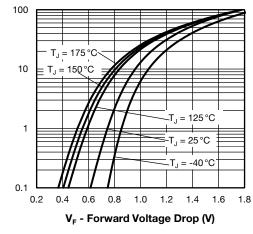


Fig. 1 - Typical Forward Voltage Drop Characteristics

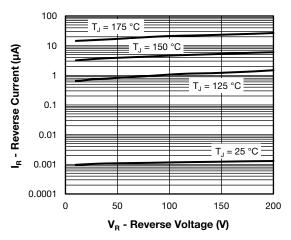


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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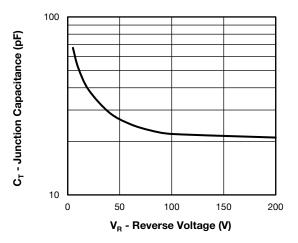


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

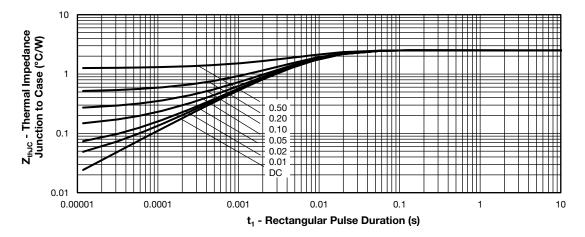
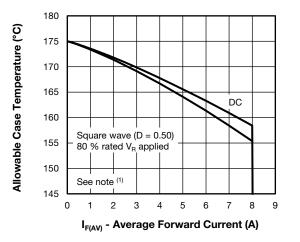
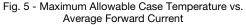


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics



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#### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

 $\begin{array}{l} \mbox{Pd} = \mbox{Forward power loss} = \mbox{I}_{F(AV)} \times \mbox{V}_{FM} \mbox{ at } (\mbox{I}_{F(AV)}/\mbox{D}) \mbox{ (see fig. 5);} \\ \mbox{Pd}_{REV} = \mbox{Inverse power loss} = \mbox{V}_{R1} \times \mbox{I}_{R} \mbox{ (1 - D); } \mbox{I}_{R} \mbox{ at } \mbox{V}_{R1} = \mbox{rated} \mbox{V}_{R} \end{array}$ 

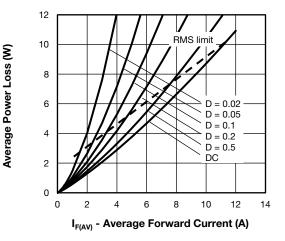


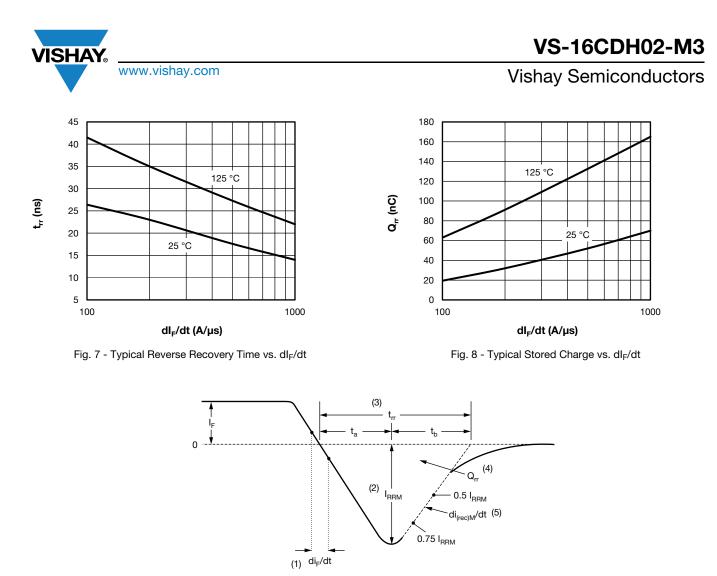
Fig. 6 - Forward Power Loss Characteristics

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- (2)  $I_{\text{RRM}}$  peak reverse recovery current
- (3)  $t_{\rm rr}$  reverse recovery time measured from zero crossing point of negative going  $I_F$  to point where a line passing through 0.75  $I_{\text{RRM}}$  and 0.50  $I_{\text{RRM}}$  extrapolated to zero current.
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (5) di<sub>(rec)M</sub>/dt peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 9 - Reverse Recovery Waveform and Definitions

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### **ORDERING INFORMATION TABLE**

| Device code | VS- | 16     | С         | D         | н        | 02      | -M3       |
|-------------|-----|--------|-----------|-----------|----------|---------|-----------|
| 201100 0000 |     |        | •         |           |          | 02      |           |
|             | 1   | 2      | 3         | 4         | 5        | 6       | 7         |
|             | 1   | - Visł | nay Sem   | nicondu   | ctors pr | oduct   |           |
|             | 2   | - Cur  | rent rati | ng (16 A  | A)       |         |           |
|             | 3   | - Circ | cuit conf | figuratio | n:       |         |           |
|             |     | C =    | commo     | on catho  | de       |         |           |
|             | 4   | - D =  | SMPD      | packag    | e        |         |           |
|             | 5   | - Pro  | cess typ  | be,       |          |         |           |
|             |     | H =    | hyperfa   | ast recov | very     |         |           |
|             | 6   | - Volt | tage coo  | de (02 =  | 200 V)   |         |           |
|             | 7   | M3     | 3 = halo  | gen-free  | e, RoHS  | -compli | iant, and |

| ORDERING INFORMATION (Example) |  |      |                                    |  |  |  |  |
|--------------------------------|--|------|------------------------------------|--|--|--|--|
| PREFERRED P/N                  | QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION |      |                                    |  |  |  |  |
| VS-16CDH02-M3/I                | 2000   | 2000 | 13" diameter plastic tape and reel |  |  |  |  |

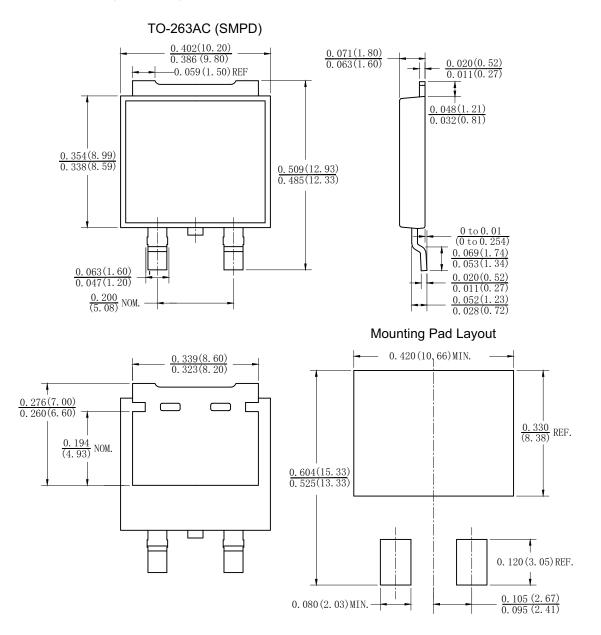
| LINKS TO RELATED DOCUMENTS |                          |  |  |  |  |
|----------------------------|--------------------------|--|--|--|--|
| Dimensions                 | www.vishay.com/doc?95604 |  |  |  |  |
| Part marking information   | www.vishay.com/doc?95566 |  |  |  |  |
| Packaging information      | www.vishay.com/doc?88869 |  |  |  |  |





TO-263AC (SMPD)

#### **DIMENSIONS** in inches (millimeters)





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